



IRF634 IRF634FP

N-CHANNEL 250V - 0.38Ω - 8A TO-220/TO-220FP
MESH OVERLAY™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
IRF634	250 V	< 0.45 Ω	8 A
IRF634FP	250 V	< 0.45 Ω	8 A

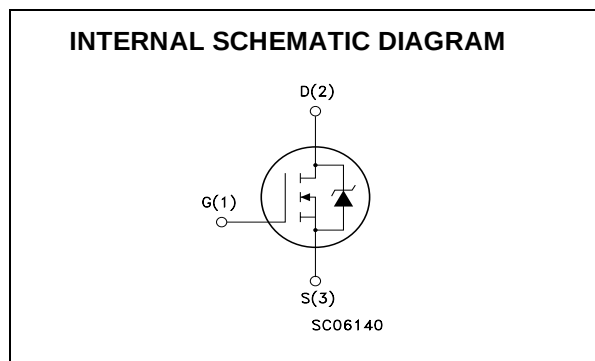
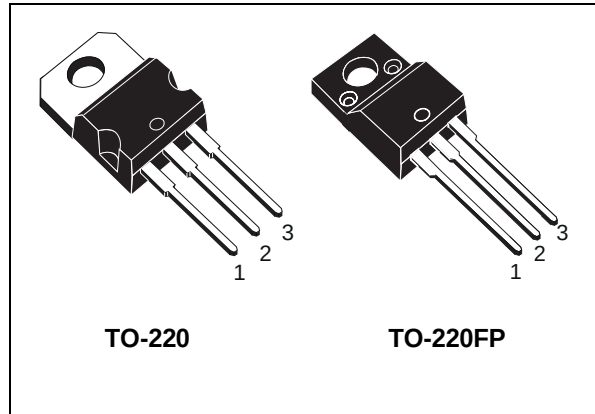
- TYPICAL R_{DS(on)} = 0.38 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performance. The new patented STrip layout coupled with the Company's proprietary edge termination structure, makes it suitable in converters for lighting applications.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-DC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT
- IDEAL FOR MONITOR's B+ FUNCTION



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		IRF634	IRF634FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	250		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	250		V
V _{GS}	Gate- source Voltage	± 20		V
I _D	Drain Current (continuous) at T _C = 25°C	8	8(*)	A
I _D	Drain Current (continuous) at T _C = 100°C	5	5(*)	A
I _{DM} (●)	Drain Current (pulsed)	32	32(*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	80	30	W
	Derating Factor	0.64	0.24	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	-	2000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 8A, di/dt ≤ 300 A/μs, V_{DD} ≤ V(BR)DSS, T_j ≤ T_{jMAX}
(*) Limited only by maximum temperature allowed

THERMAL DATA

		TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	1.56	4.11	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	8	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	300	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	250			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 4 A		0.38	0.45	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)} max, I _D = 4A	7	8		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		770		pF
C _{oss}	Output Capacitance			118		pF
C _{rss}	Reverse Transfer Capacitance			48		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 125\text{ V}$, $I_D = 4\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		13		ns
t_r	Rise Time			18		ns
Q_g	Total Gate Charge	$V_{DD} = 200\text{ V}$, $I_D = 8\text{ A}$, $V_{GS} = 10\text{ V}$		37	51.8	nC
Q_{gs}	Gate-Source Charge			5.2		nC
Q_{gd}	Gate-Drain Charge			14.8		nC

SWITCHING OFF

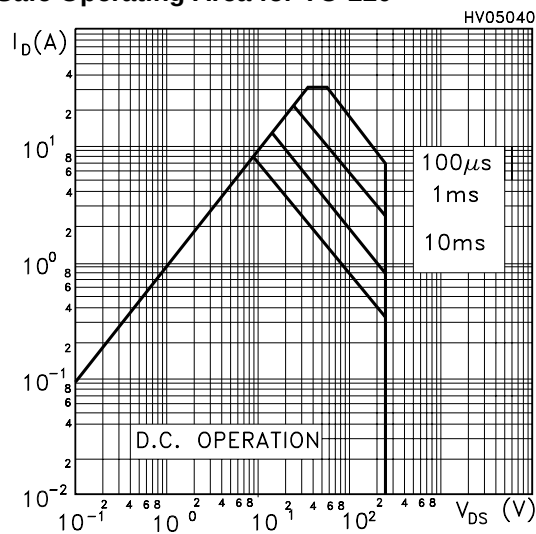
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(Voff)}$	Turn-off Delay Time	$V_{DD} = 125\text{ V}$, $I_D = 4\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		51		ns
t_f	Fall Time			16		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 200\text{ V}$, $I_D = 8\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		12.5		ns
t_f	Fall Time			12.5		ns
t_c	Cross-over Time			28		ns

SOURCE DRAIN DIODE

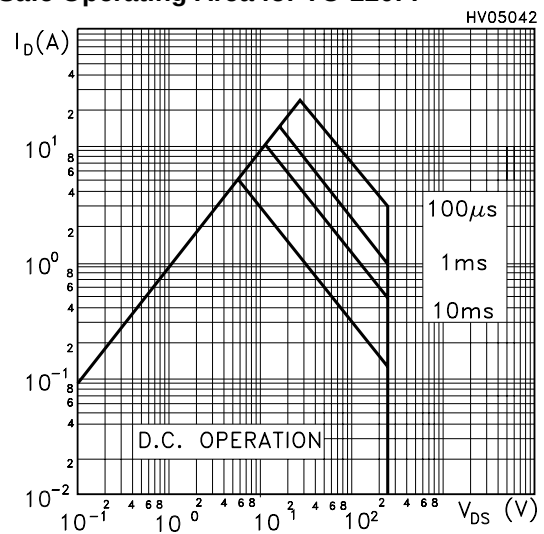
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				32	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 8\text{ A}$, $V_{GS} = 0$			1.7	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$, $T_J = 150^\circ\text{C}$ (see test circuit, Figure 5)		198		ns
Q_{rr}	Reverse Recovery Charge			1.1		μC
I_{RRM}	Reverse Recovery Current			11.3		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

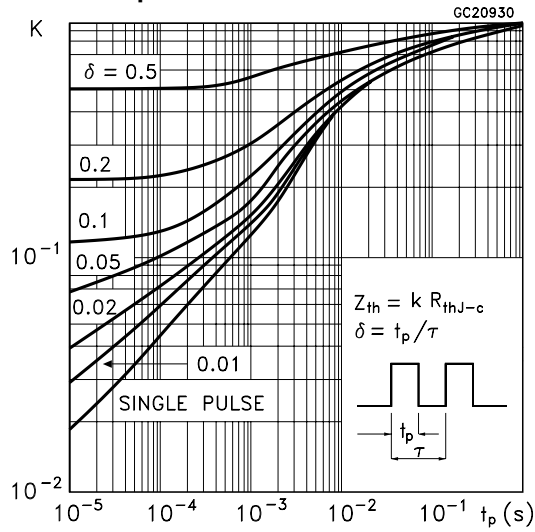
Safe Operating Area for TO-220



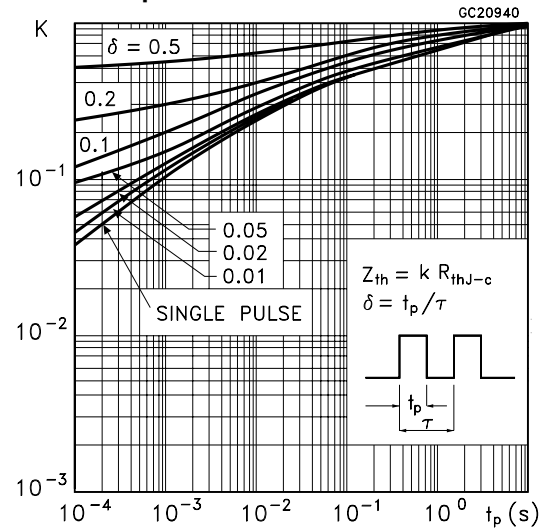
Safe Operating Area for TO-220FP



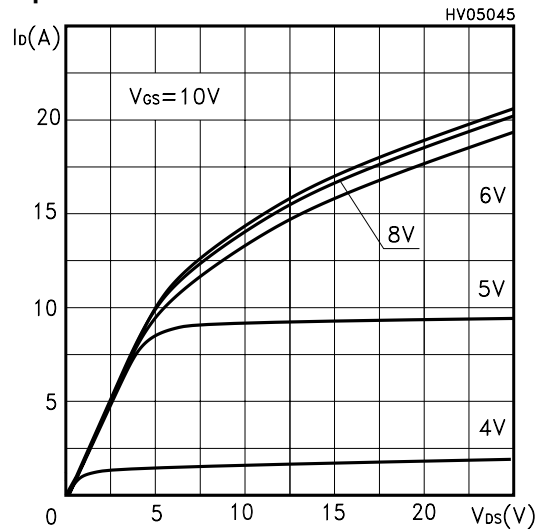
Thermal Impedance for TO-220



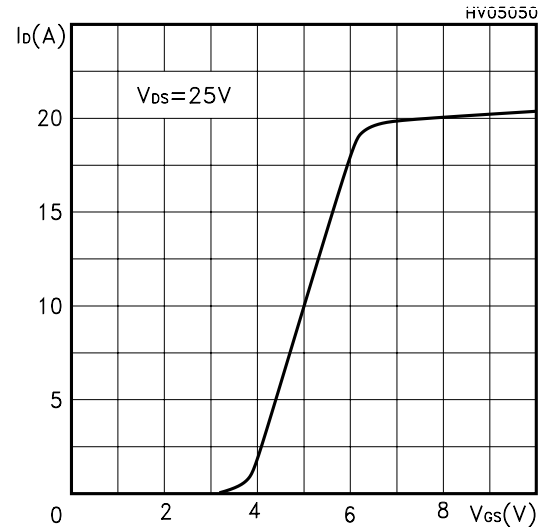
Thermal Impedance for TO-220FP



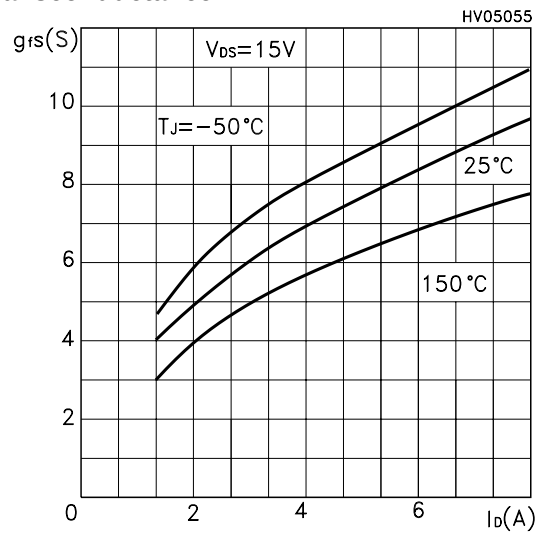
Output Characteristics



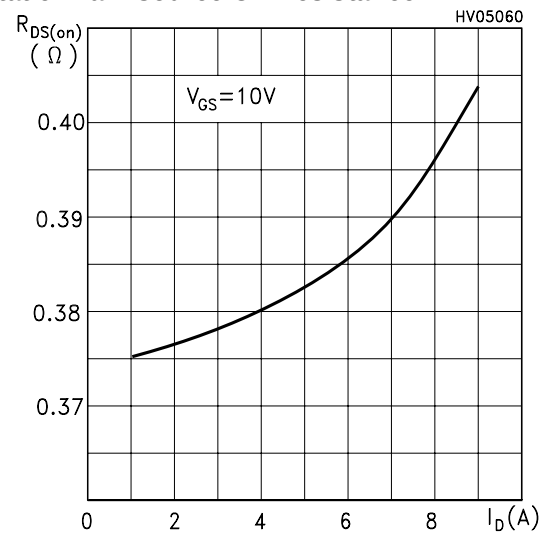
Transfer Characteristics



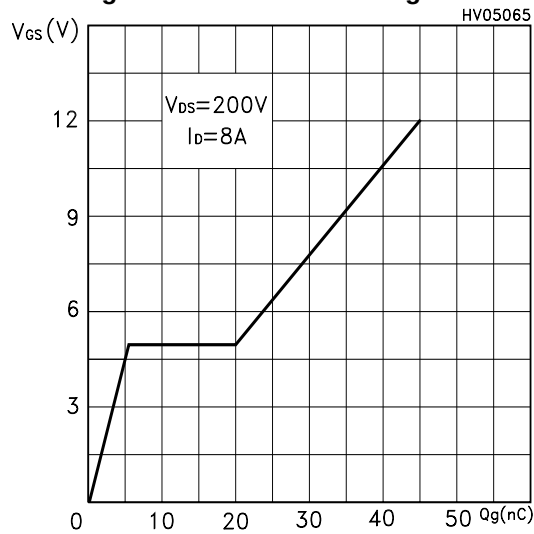
Transconductance



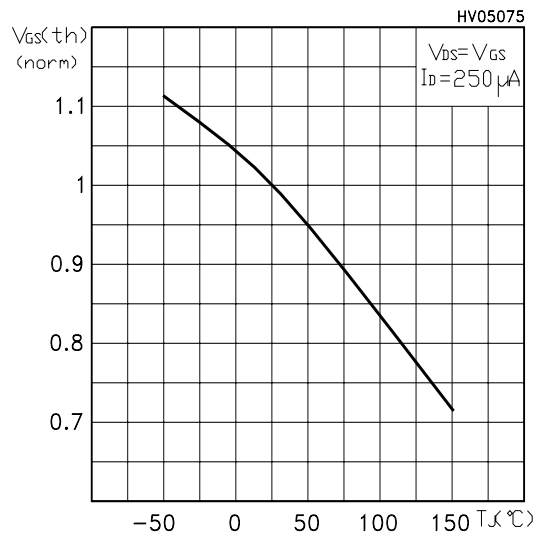
Static Drain-source On Resistance



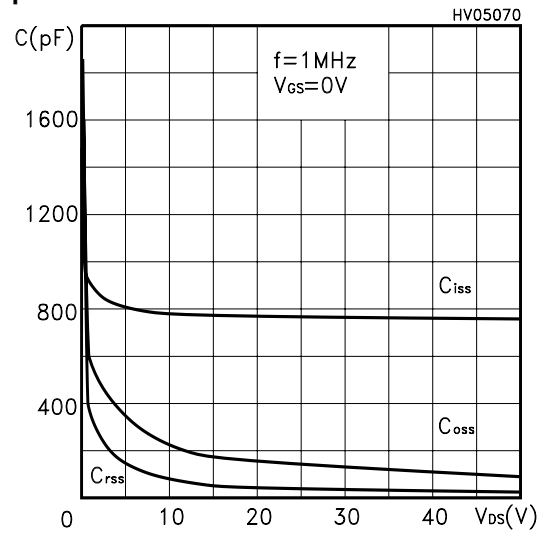
Gate Charge vs Gate-source Voltage



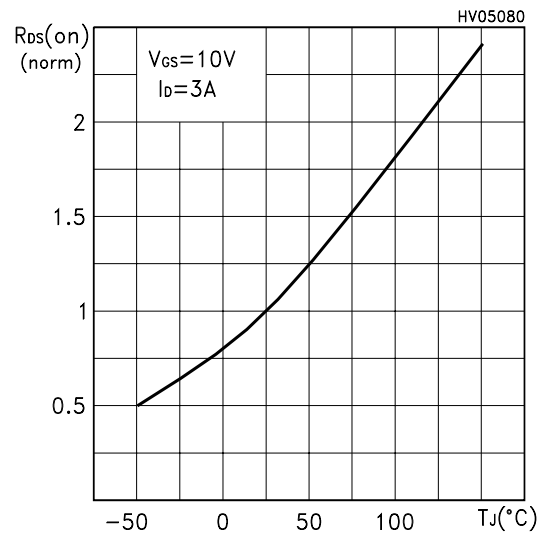
Normalized Gate Threshold Voltage vs Temp.



Capacitance Variations



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

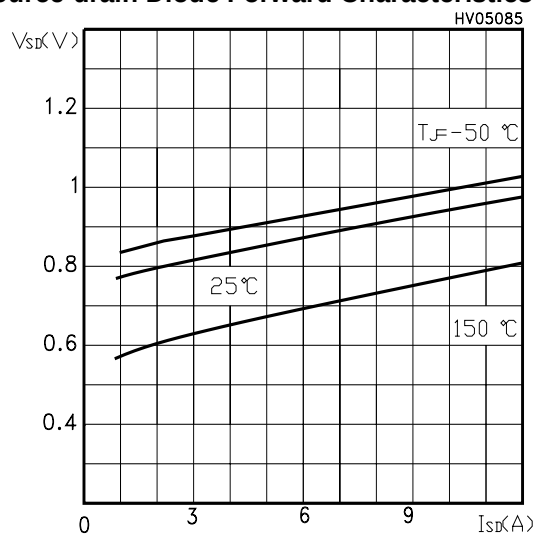


Fig. 1: Unclamped Inductive Load Test Circuit

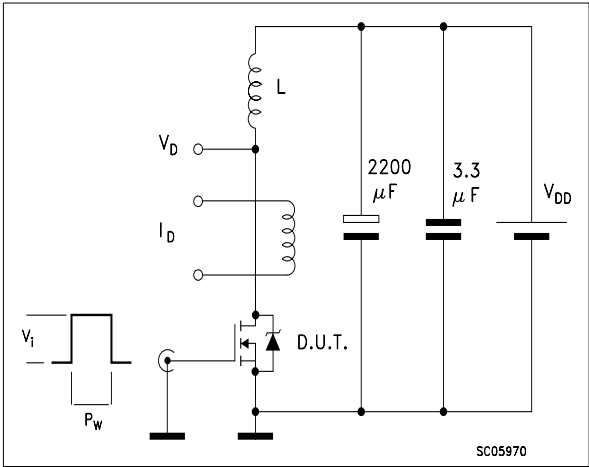


Fig. 2: Unclamped Inductive Waveform

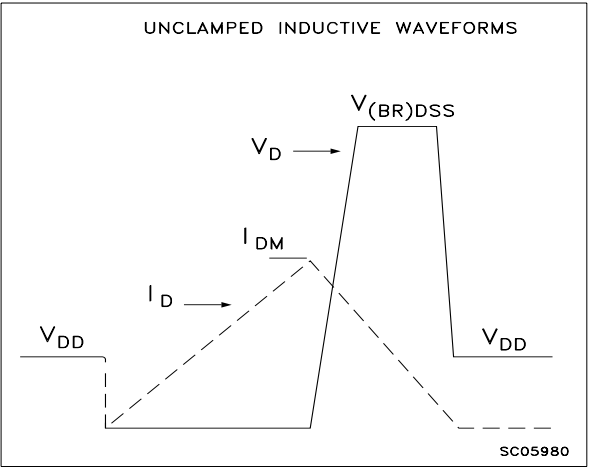


Fig. 3: Switching Times Test Circuit For Resistive Load

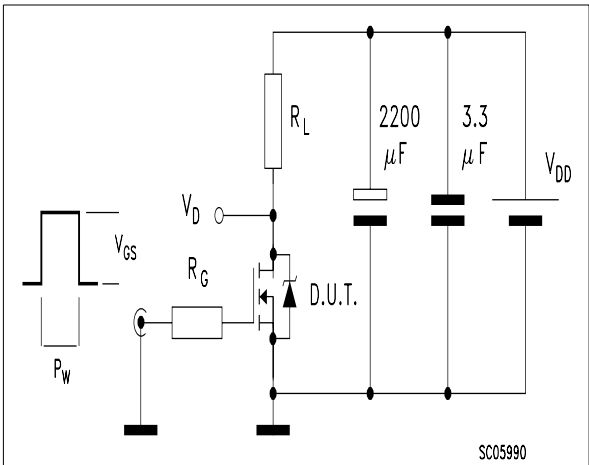


Fig. 4: Gate Charge test Circuit

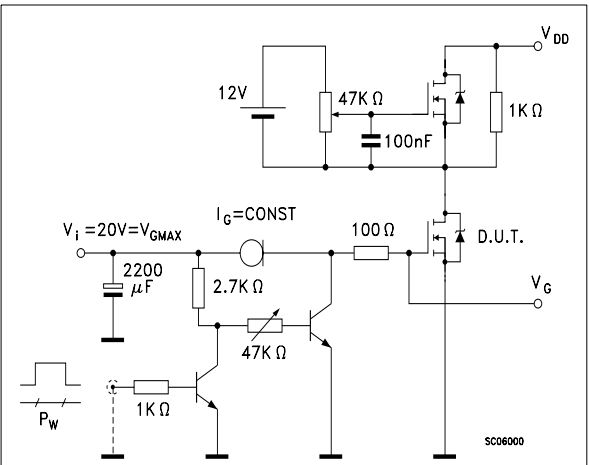
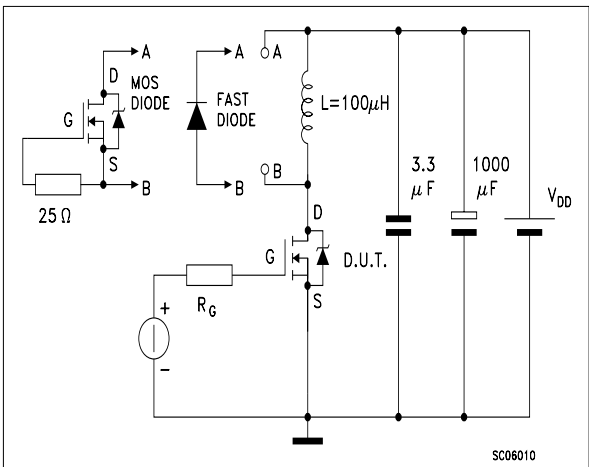
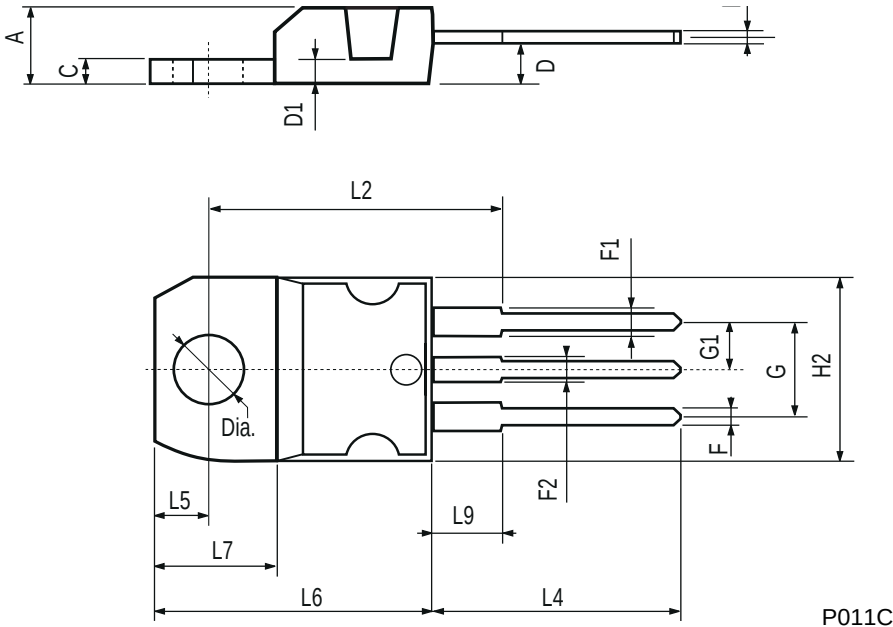


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



The technical drawing consists of two views of a mechanical component. The top view is a side profile showing a stepped shaft. It has a main body with a stepped end, a central section with a circular feature, and a long, thin shaft extending to the right. Dimensions labeled are A (total height), B (height of the central section), D (diameter of the thin shaft), and E (thickness of the thin shaft). The bottom view is a front elevation showing a rectangular block with a central slot. Dimensions labeled are L2 (width of the block), L3 (total length), L4 (length of the thin shaft), L5 (length of the block), L6 (length of the central section), L7 (length of the slot), H (height of the block), and G (height of the thin shaft). Features labeled are F1 (top of the thin shaft), F (middle of the thin shaft), F2 (bottom of the thin shaft), and three numbered points 1, 2, 3 (locations on the thin shaft).

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